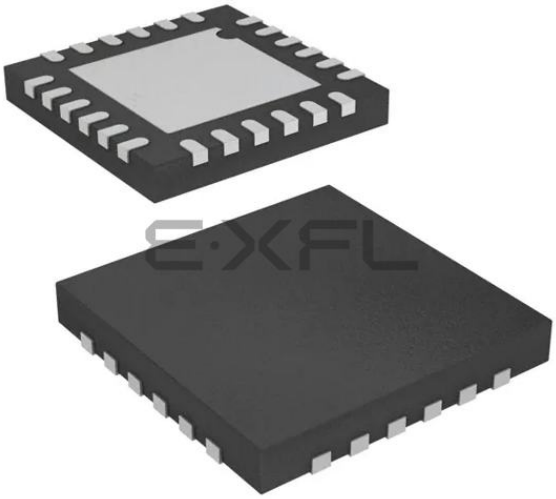

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Embedded - Microcontrollers - Application Specific: Tailored Solutions for Precision and Performance

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What Are Embedded - Microcontrollers - Application Specific?

Application-specific microcontrollers are engineered to

Details	
Product Status	Active
Applications	USB Type C
Core Processor	ARM® Cortex®-M0
Program Memory Type	FLASH (64kB)
Controller Series	-
RAM Size	8K x 8
Interface	I²C, SPI, UART
Number of I/O	12
Voltage - Supply	3V ~ 24.5V
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	24-UFQFN Exposed Pad
Supplier Device Package	24-QFN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cypd3174-24lqxq

Functional Overview

MCU Subsystem

CPU

The Cortex-M0 CPU in EZ-PD CCG3PA is part of the 32-bit MCU subsystem, which is optimized for low-power operation with extensive clock gating.

The CPU also includes a serial wire debug (SWD) interface, which is a 2-wire form of JTAG. The debug configuration used for EZ-PD CCG3PA has four break-point (address) comparators and two watchpoint (data) comparators.

Flash

The EZ-PD CCG3PA device has a flash module with one bank of 64-KB flash, a flash accelerator, tightly coupled to the CPU to improve average access times from the flash block.

SROM

A supervisory ROM that contains boot and configuration routines is provided.

USB-PD Subsystem (SS)

The USB-PD subsystem provides the interface to the Type-C USB port. This subsystem comprises a current sense amplifier, a high-voltage regulator, OVP, OCP, and supply switch blocks. This subsystem also includes all ESD required and supported on the Type-C port.

USB-PD Physical Layer

The USB-PD Physical Layer consists of a transmitter and receiver that communicate BMC-encoded data over the CC channel based on the PD 3.0 standard. All communication is half-duplex. The Physical Layer or PHY practices collision avoidance to minimize communication errors on the channel.

The USB-PD block includes all termination resistors (R_P and R_D) and their switches as required by the USB-PD spec. R_P and R_D resistors are required to implement connection detection, plug orientation detection, and for establishing USB DFP/UFP roles. The R_P resistor is implemented as a current source.

According to the USB Type-C spec, a Type-C controller such as CCG3PA must present certain termination resistors depending on its role in its unpowered state. The Sink role in a power bank application requires R_D resistors to be present on the CC pins whereas the DFP role, as in a power adapter, requires both CC lines to be open. To be flexible for such applications, CCG3PA includes the resistors required in the unpowered state on separate pads or pins. The dead battery R_D resistors are available on separate pads. The dead battery R_D is implemented as a bond option on parts for Power Bank applications. In these parts, each CC pin is bonded out together with its corresponding dead battery R_D resistor. On part numbers for the DFP application, the CC pins are not bonded with the dead battery R_D.

ADC

The ADC is a low-footprint 8-bit SAR ADC that is available for general-purpose A-D conversion applications in the chip. This ADC can be accessed from all GPIOs and the DP/DM pins through an on-chip analog mux. CCG3PA contains two instances of the ADC. The voltage reference for the ADCs is generated either from the VDDD supply or from internal bandgap. When sensing the GPIO pin voltage with an ADC, the pin voltage cannot exceed the VDDIO supply value.

Charger Detection

The two charger detection blocks connected to the two pairs of DP/DM pins allow CCG3PA to detect conventional battery chargers conforming to BC 1.2, and the following proprietary charger specifications: Apple, Qualcomm's QuickCharge 4.0, and Samsung AFC.

VBUS Overcurrent and Overvoltage Protection

The CCG3PA chip has an integrated hardware block for VBUS overvoltage protection (OVP)/overcurrent protection (OCP) with configurable thresholds and response times on the Type C port.

VBUS Short Protection

CCG3PA provides four VBUS short protection pins: CC1, CC2, P2.2, and P2.3. These pins are protected from accidental shorts to high-voltage VBUS. Accidental shorts may occur because the CC1 and CC2 pins are placed next to the VBUS pins in the USB Type-C connector. A Power Delivery controller without the high-voltage VBUS short protection will be damaged in the event of accidental shorts. When the protection circuit is triggered, CCG3PA can handle up to 17 V forever and between 17 V to 22 VDC for 1000 hours on the OVT pins. When a VBUS short event occurs on the CC pins, a temporary high-ringing voltage is observed due to the RLC elements in the USB Type-C cable. Without CCG3PA connected, this ringing voltage can be twice (44 V) the maximum VBUS voltage (21.5 V). However, when CCG3PA is connected, it is capable of clamping temporary high-ringing voltage and protecting the CC pin using IEC ESD protection diodes.

Low-side Current Sense Amplifier (CSA)

The CCG3PA chip also has an integrated low-side current sense amplifier that is capable of detecting current in the order of 100 mA across a 5 mΩ external resistor. It also supports constant current mode of operation in power adapter application as a provider.

PFET Gate Drivers on VBUS Path

CCG3PA has two integrated PFET gate drivers to drive external PFETs on the VBUS provider and consumer path. The VBUS_P_CTRL gate driver has an active pull-up, and thus can drive high, low or High-Z.

The VBUS_C_CTRL gate driver can drive only low or high-Z, thus requiring an external pull-up. These pins are VBUS voltage-tolerant.

VBUS Discharge FETs

CCG3PA also has two integrated VBUS discharge FETs used to discharge VBUS to meet the USB-PD specification timing on a detach condition. VBUS Discharge FET on the provider side can be used to accelerate the ramp down of VBUS to default 5V on the secondary side.

Voltage (VBUS) Regulation

CCG3PA contains an integrated feedback control circuitry (for AC/DC applications) for secondary side control with analog regulation of the feedback/cathode pins to achieve the appro-

priate voltage on VBUS pin as per the negotiated contract with the peer device over Type-C.

Integrated Digital Blocks

Serial Communication Blocks (SCB)

EZ-PD CCG3PA has two SCBs, which can be configured to implement an I^2C, SPI, or UART interface. The hardware I^2C blocks implement full multi-master and slave interfaces capable of multimaster arbitration. In the SPI mode, the SCB blocks can be configured to act as master or slave.

In the I^2C mode, the SCB blocks are capable of operating at speeds of up to 1 Mbps (Fast Mode Plus) and have flexible buffering options to reduce interrupt overhead and latency for the CPU. These blocks also support I^2C that creates a mailbox address range in the memory of EZ-PD CCG3PA and effectively reduce I^2C communication to reading from and writing to an array in memory. In addition, the blocks support 8-deep FIFOs for receive and transmit which, by increasing the time given for the CPU to read data, greatly reduce the need for clock stretching caused by the CPU not having read data on time.

The I^2C peripherals are compatible with the I^2C Standard-mode, Fast-mode, and Fast-mode Plus devices as defined in the NXP I^2C-bus specification and user manual (UM10204). The I^2C bus I/Os are implemented with GPIO in open-drain modes.

The I^2C port on the SCB blocks of EZ-PD CCG3PA are not completely compliant with the I^2C spec in the following aspects:

- The GPIO cells for SCB 1's I^2C port are not overvoltage-tolerant and, therefore, cannot be hot-swapped or powered up independently of the rest of the I^2C system.
- Fast-mode Plus has an I_{OL} specification of 20 mA at a V_{OL} of 0.4 V. The GPIO cells can sink a maximum of 8-mA I_{OL} with a V_{OL} maximum of 0.6 V.
- Fast-mode and Fast-mode Plus specify minimum Fall times, which are not met with the GPIO cell; Slow strong mode can help meet this spec depending on the bus load.

Timer/Counter/PWM Block (TCPWM)

EZ-PD CCG3PA has four TCPWM blocks. Each implements a 16-bit timer, counter, pulse-width modulator (PWM), and quadrature decoder functionality. The block can be used to measure the period and pulse width of an input signal (timer), find the number of times a particular event occurs (counter), generate PWM signals, or decode quadrature signals.

I/O Subsystem

EZ-PD CCG3PA has up to 12 GPIOs of which, some of them can be re-purposed to support functions of SCB (I^2C, UART, SPI). GPIO pins P0.0 and P0.1 are overvoltage-tolerant (OVT) (upto 7V).

The GPIO block implements the following:

- Seven drive strength modes:
  - Input only
  - Weak pull-up with strong pull-down
  - Strong pull-up with weak pull-down
  - Open drain with strong pull-down
  - Open drain with strong pull-up
  - Strong pull-up with strong pull-down
  - Weak pull-up with weak pull-down
- Input threshold select (CMOS or LVTTL)
- Individual control of input and output buffer enabling/disabling in addition to the drive strength modes
- Hold mode for latching previous state (used for retaining I/O state in Deep Sleep mode)
- Selectable slew rates for dV/dt related noise control to improve EMI

During power-on and reset, the I/O pins are forced to the disable state so as not to crowbar any inputs and/or cause excess turn-on current. A multiplexing network known as a high-speed I/O matrix is used to multiplex between various signals that may connect to an I/O pin.

Port pins P1.0 and P1.1 can be configured to indicate Fault for OCP/SCP/OVP/UVP conditions. Any two fault conditions can be mapped to two GPIOs or all the four faults can be OR'ed to indicate over one GPIO.

Figure 2. Pinout of 24-QFN Package (Top View)

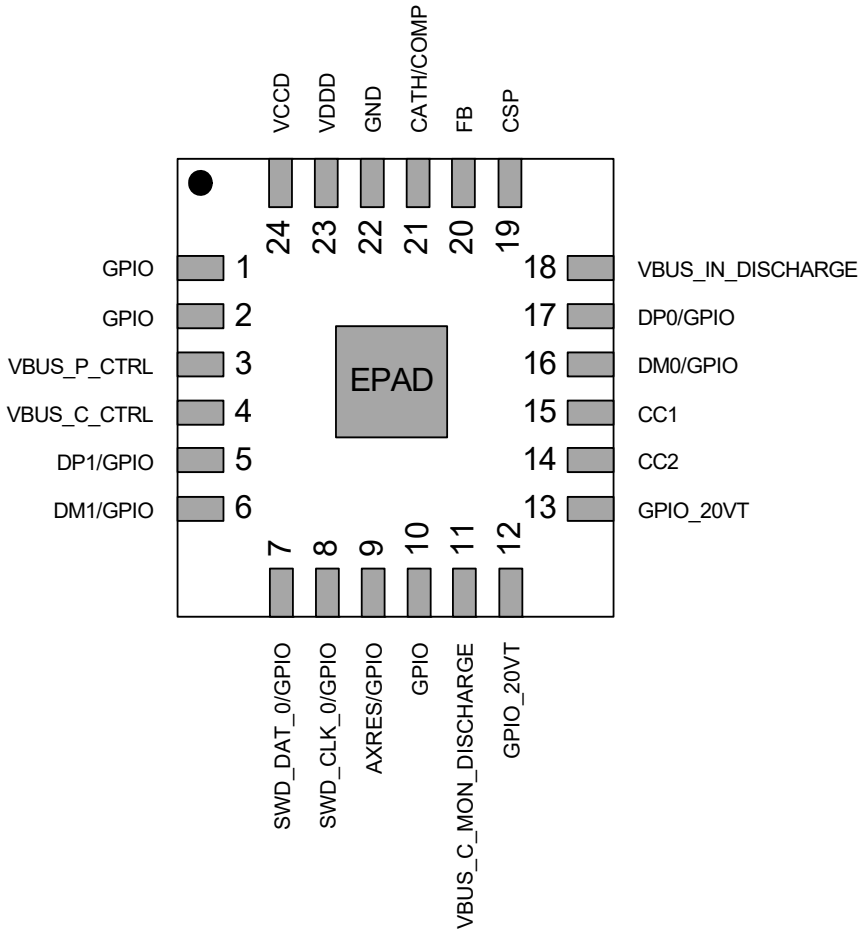
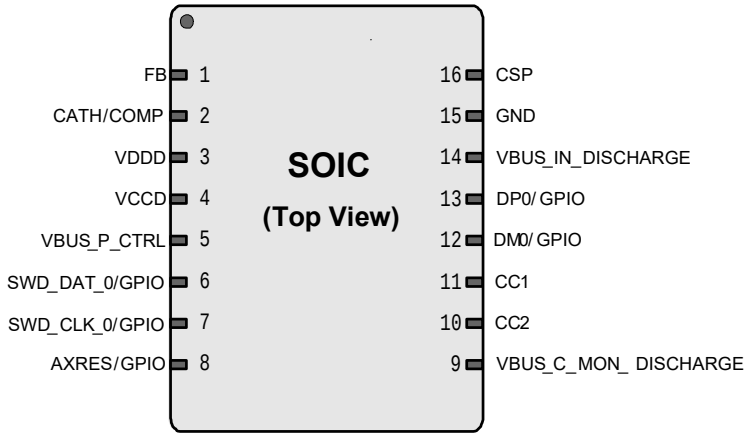


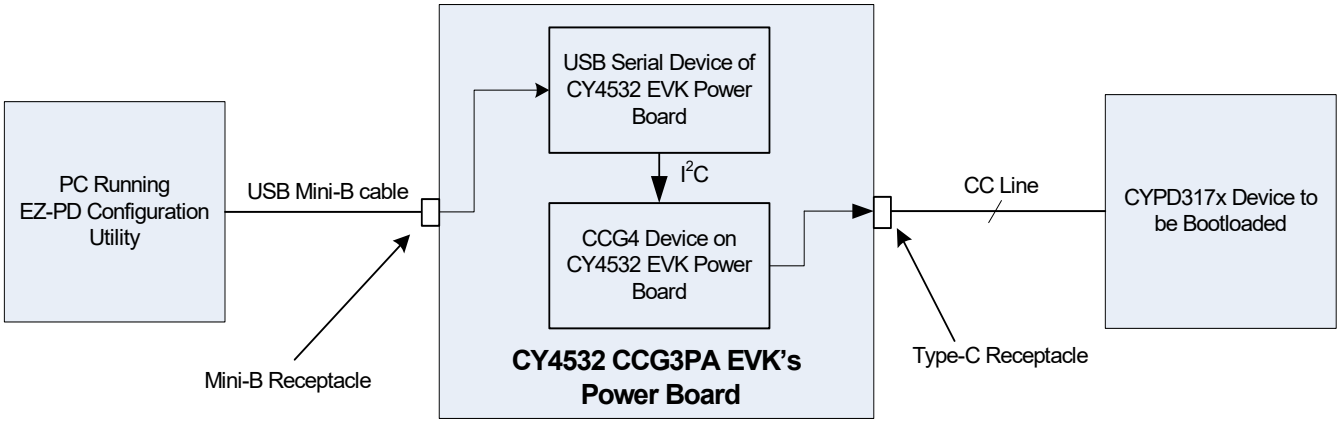
Figure 3. Pinout of 16-SOIC Package (Top View)



Application Firmware Update over CC Interface

For bootloading CCG3PA applications, the CY4532 CCG3PA EVK can be used to send programming and configuration data as Cypress specific Vendor Defined Messages (VDMs) over the CC line. The CY4532 CCG3PA EVK's Power Board is connected to the system containing CCG3PA device on one end and a Windows PC running the EZ-PD™ Configuration Utility as shown in Figure 5 on the other end to bootload the CCG3PA device.

Figure 5. Application Firmware Update over CC Interface



Application Diagrams

Figure 6 and Figure 7 show the application diagrams of CCG3PA-based Power Adapter with Opto-Coupler Feedback control using 16-pin SOIC and 24-pin QFN parts respectively. In an opto-feedback power adapter, CCG3PA implements a shunt regulator and the feedback to the primary controller is through an opto-coupler. The current drawn through the CATH path is proportional to the potential difference between FB pin and the internal bandgap reference voltage. At default 5-V VBUS, the FB pin will be held at the voltage set by the bandgap reference voltage using internal VBUS resistor dividers.

If VBUS needs to be changed from default 5 V, using internal IDACs and an error amplifier, CCG3PA draws a proportional current through the CATH pin. This in turn gets coupled to the primary controller through the opto-coupler.

Figure 6. CCG3PA Based Power Adapter Application Diagram with Opto Coupler Feedback Control (16-pin SOIC Device)

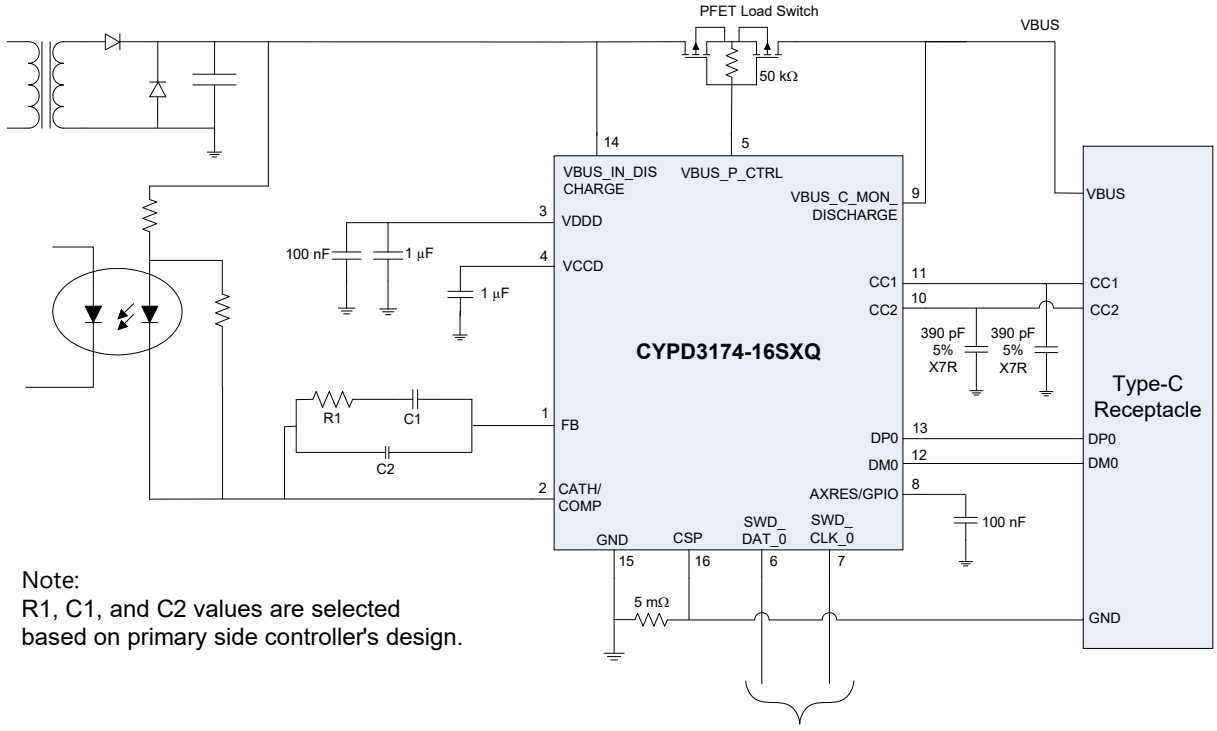
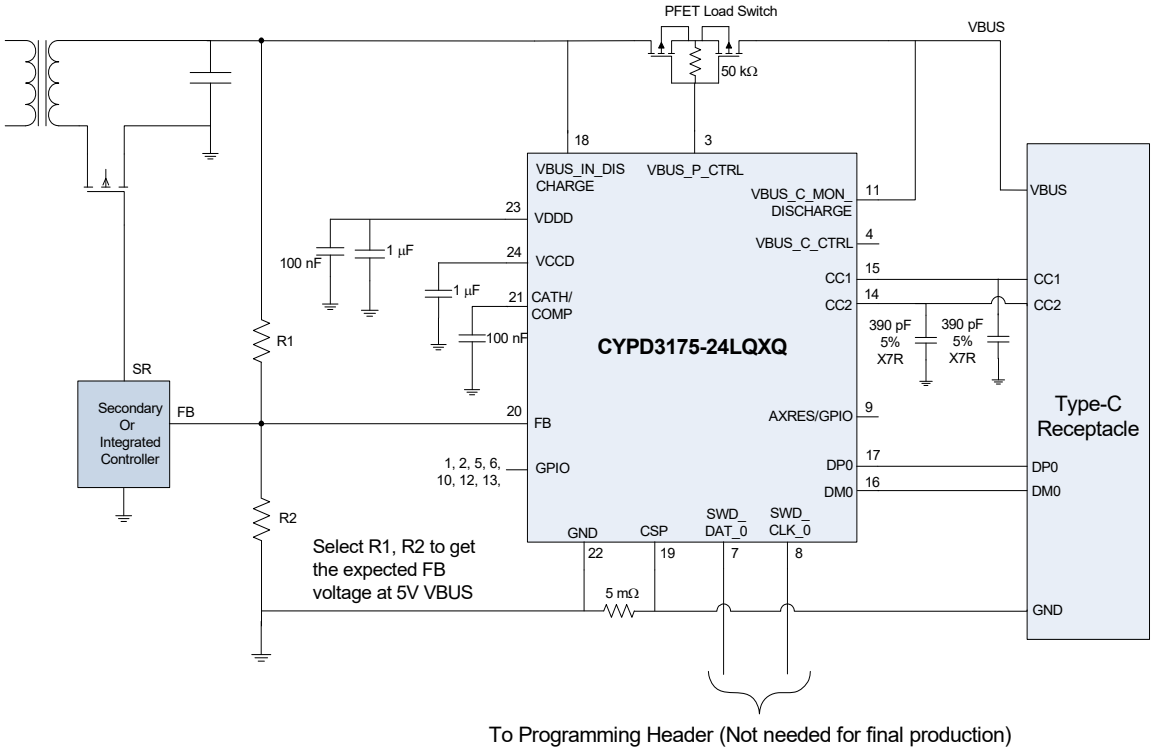


Figure 8 shows the application diagram of CCG3PA based power adapter with Direct Feedback control. In this application, VBUS is maintained at a constant voltage. The default value of VBUS upon power up (which is usually at 5 V) is set up by choosing the appropriate resistor divider that will set the FB node at a voltage expected by the secondary controller.

Feedback node is regulated using internal IDACs. Whenever a change in VBUS voltage is needed, CCG3PA will either source or sink a proportional current at feedback node, based on the amount of voltage change needed.

Figure 8. CCG3PA Based Power Adapter Application Diagram with Direct Feedback Control



Electrical Specifications

Absolute Maximum Ratings

Table 4. Absolute Maximum Ratings

Parameter	Description	Min	Typ	Max	Units	Details/Conditions
V_{BUS_MAX}	Max supply voltage relative to V_{SS} on VBUS_IN_DISCHARGE and VBUS_C_MON_DISCHARGE pins	–	–	30	V	Absolute max
V_{DDD_MAX}	Max supply voltage relative to V_{SS}	–	–	6	V	
$V_{CC\_PIN\_ABS}$	Max voltage on CC1, CC2 pins and port pins P2.2 and P2.3 for applicable devices	–	–	22[6]	V	
V_{GPIO_ABS}	GPIO voltage	–0.5	–	V_{DDD} +0.5	V	
I_{GPIO_ABS}	Maximum current per GPIO	–25	–	25	mA	
$I_{GPIO\_injection}$	GPIO injection current, Max for $V_{IH} > V_{DDD}$, and Min for $V_{IL} < V_{SS}$	–0.5	–	0.5	mA	Absolute max, current injected per pin
$V_{GPIO\_OVT\_ABS}$	OVT GPIO voltage	–0.5	–	6	V	Applicable to port pins P0.0 and P0.1
ESD_HBM	Electrostatic discharge human body model	2200	–	–	V	–
ESD_CDM	Electrostatic discharge charged device model	500	–	–	V	–
LU	Pin current for latch-up	–100	–	100	mA	–
ESD_IEC_CON	Electrostatic discharge IEC61000-4-2	8000	–	–	V	Contact discharge on CC1, CC2, VBUS, P2.2 and P2.3 pins
ESD_IEC_AIR	Electrostatic discharge IEC61000-4-2	15000	–	–	V	Air discharge for DPLUS, DMINUS, CC1, CC2, VBUS, P2.2 and P2.3 pins

Device-Level Specifications

All specifications are valid for –40 °C ≤ T_A ≤ 105 °C and T_J ≤ 120 °C, except where noted.

Table 5. DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID.PWR#2	V_{DDD}	Power Supply Input Voltage	2.7	–	5.5	V	Sink mode, –40 °C ≤ T_A ≤ 105 °C.
SID.PWR#2_A	V_{DDD}	Power Supply Input Voltage	3.0	–	5.5	V	Source mode, –40 °C ≤ T_A ≤ 105 °C.
SID.PWR#3	V_{BUS_IN}	Power Supply Input Voltage	3.0	–	24.5	V	–40 °C ≤ T_A ≤ 105 °C.
SID.PWR#5	V_{CCD}	Output Voltage for core Logic	–	1.8	–	V	–
SID.PWR#13	C_{exc}	Power supply decoupling capacitor for V_{DDD}	0.8	1	–	µF	X5R ceramic or better
SID.PWR#14	C_{exv}	Power supply decoupling capacitor for VBUS_IN_DISH-CARGE	–	0.1	–	µF	X5R ceramic or better

Note
6. As per USB PD specification, maximum allowed VBUS = 21.5V.

I/O

Table 7. I/O DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID.GIO#37	V_{IH_CMOS}	Input voltage HIGH threshold	0.7 × V_{DDD}	–	–	V	CMOS input
SID.GIO#38	V_{IL_CMOS}	Input voltage LOW threshold	–	–	0.3 × V_{DDD}	V	CMOS input
SID.GIO#39	$V_{IH\_VDDD2.7-}$	LVTTL input, V_{DDD} < 2.7 V	0.7× V_{DDD}	–	–	V	–
SID.GIO#40	$V_{IL\_VDDD2.7-}$	LVTTL input, V_{DDD} < 2.7 V	–	–	0.3 × V_{DDD}	V	–
SID.GIO#41	$V_{IH\_VDDD2.7+}$	LVTTL input, V_{DDD} ≥ 2.7 V	2.0	–	–	V	–
SID.GIO#42	$V_{IL\_VDDD2.7+}$	LVTTL input, V_{DDD} ≥ 2.7 V	–	–	0.8	V	–
SID.GIO#33	V_{OH_3V}	Output voltage HIGH level	V_{DDD} –0.6	–	–	V	I_{OH} = 4 mA at 3-V V_{DDD}
SID.GIO#36	V_{OL_3V}	Output voltage LOW level	–	–	0.6	V	I_{OL} = 10 mA at 3-V V_{DDD}
SID.GIO#5	R_{PU}	Pull-up resistor value	3.5	5.6	8.5	kΩ	+25 °C T_A, all V_{DDD}
SID.GIO#6	R_{PD}	Pull-down resistor value	3.5	5.6	8.5	kΩ	+25 °C T_A, all V_{DDD}
SID.GIO#16	I_{IL}	Input leakage current (absolute value)	–	–	2	nA	+25 °C T_A, 3-V V_{DDD}
SID.GIO#17	C_{PIN_A}	Max pin capacitance	–	–	22	pF	Capacitance on DP0, DM0, DP1, DMI pins. Guaranteed by characterization.
SID.GIO#17A	C_{PIN}	Max pin capacitance	–	3	7	pF	–40°C to +85°C T_A, All V_{DDD}, all other I/O_S. Guaranteed by characterization.
SID.GIO#43	V_{HYSTTL}	Input hysteresis, LVTTL V_{DDD} > 2.7 V	15	40	–	mV	Guaranteed by characterization.
SID.GIO#44	$V_{HYSCMOS}$	Input hysteresis CMOS	0.05 × V_{DDD}	–	–	mV	V_{DDD} < 4.5 V. Guaranteed by characterization.
SID69	I_{DIODE}	Current through protection diode to V_{DDD}/V_{SS}	–	–	100	µA	Guaranteed by design.
SID.GIO#45	I_{TOT_GPIO}	Maximum total sink chip current	–	–	85	mA	Guaranteed by design.
OVT							
SID.GIO#46	I_{IHS}	Input current when Pad > V_{DDD} for OVT inputs	–	–	10.00	µA	Per I^2C specification

Table 8. I/O AC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID70	T_{RISEF}	Rise time in Fast Strong mode	2	–	12	ns	3.3-V V_{DDD}, C_{load} = 25 pF
SID71	T_{FALLF}	Fall time in Fast Strong mode	2	–	12	ns	3.3-V V_{DDD}, C_{load} = 25 pF

Table 9. GPIO_20VT DC Specifications (Applicable to port pins P2.2 and P2.3 only)

(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details / Conditions
SID.GPIO_20VT#4	GPIO_20VT_I_LU	GPIO_20VT Latch up current limits	–140	–	140	mA	Max / min current in to any input or output, pin-to-pin, pin-to-supply
SID.GPIO_20VT#5	GPIO_20VT_RPU	GPIO_20VT Pull-up resistor value	1	–	25	kΩ	+25 °C T_A, 1.4 V to GPIO_20VT_Voh(min)
SID.GPIO_20VT#6	GPIO_20VT_RPD	GPIO_20VT Pull-down resistor value	2.5	–	20	kΩ	+25°C T_A, 1.4-V to V_{DDD}
SID.GPIO_20VT#16	GPIO_20VT_IIL	GPIO_20VT Input leakage current (absolute value)	–	–	2	nA	+25°C T_A, 3-V V_{DDD}
SID.GPIO_20VT#17	GPIO_20VT_CPIN	GPIO_20VT pin capacitance	15	–	25	pF	–40 °C to +85 °C T_A, All V_{DDD}, F = 1 MHz
SID.GPIO_20VT#36	GPIO_20VT_Vol	GPIO_20VT Output Voltage low level.	–	–	0.4	V	I_{OL} = 2 mA
SID.GPIO_20VT#41	GPIO_20VT_Vih_LVTTL	GPIO_20VT LVTTL Input Voltage high level.	2	–	–	V	$V_{DDD} \geq 2.7$ V
SID.GPIO_20VT#42	GPIO_20VT_Vil_LVTTL	GPIO_20VT LVTTL Input Voltage low level.	–	–	0.8	V	$V_{DDD} \geq 2.7$ V
SID.GPIO_20VT#43	GPIO_20VT_Vhysttl	GPIO_20VT Input hysteresis LVTTL	15	40	–	mV	$V_{DDD} \geq 2.7$ V
SID.GPIO_20VT#69	GPIO_20VT_IDIODE	GPIO_20VT Current through protection diode to V_{DDD}/V_{SS}	–	–	100	µA	

Table 10. GPIO_20VT AC Specifications (Applicable to port pins P2.2 and P2.3 only)

(Guaranteed by Characterization)

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details / Conditions
SID.GPIO_20VT#70	GPIO_20VT_TriseF	GPIO_20VT Rise time in Fast Strong Mode	1	–	45	ns	All V_{DDD}, C_{load} = 25 pF
SID.GPIO_20VT#71	GPIO_20VT_TfallF	GPIO_20VT Fall time in Fast Strong Mode	2	–	15	ns	All V_{DDD}, C_{load} = 25 pF

Digital Peripherals

The following specifications apply to the Timer/Counter/PWM peripherals in the Timer mode.

Pulse Width Modulation (PWM) for GPIO Pins

Table 11. PWM AC Specifications (Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID.TCPWM.3	$T_{CPWMFREQ}$	Operating frequency	–	–	Fc	MHz	Fc max = CLK_SYS. Maximum = 48 MHz.
SID.TCPWM.4	$T_{PWMENEXT}$	Input trigger pulse width	2/Fc	–	–	ns	For all trigger events
SID.TCPWM.5	T_{PWMEXT}	Output trigger pulse width	2/Fc	–	–	ns	Minimum possible width of Overflow, Underflow, and CC (Counter equals Compare value) outputs
SID.TCPWM.5A	T_{CRES}	Resolution of counter	1/Fc	–	–	ns	Minimum time between successive counts
SID.TCPWM.5B	PWM_{RES}	PWM resolution	1/Fc	–	–	ns	Minimum pulse width of PWM output
SID.TCPWM.5C	Q_{RES}	Quadrature inputs resolution	1/Fc	–	–	ns	Minimum pulse width between quadrature-phase inputs

I^2C

Table 12. Fixed I^2C DC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID149	I_{I2C1}	Block current consumption at 100 kHz	–	–	100	µA	–
SID150	I_{I2C2}	Block current consumption at 400 kHz	–	–	135	µA	–
SID151	I_{I2C3}	Block current consumption at 1 Mbps	–	–	310	µA	–
SID152	I_{I2C4}	I^2C enabled in Deep Sleep mode	–	1.4	–	µA	–

Table 13. Fixed I^2C AC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID153	F_{I2C1}	Bit rate	–	–	1	Mbps	–

Table 14. Fixed UART DC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID160	I_{UART1}	Block current consumption at 100 kbps	–	–	20	µA	–
SID161	I_{UART2}	Block current consumption at 1000 kbps	–	–	312	µA	–

Table 15. Fixed UART AC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID162	F_{UART}	Bit rate	–	–	1	Mbps	–

Table 16. Fixed SPI DC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID163	I_{SPI1}	Block current consumption at 1 Mb/s	–	–	360	µA	–
SID164	I_{SPI2}	Block current consumption at 4 Mb/s	–	–	560	µA	–
SID165	I_{SPI3}	Block current consumption at 8 Mb/s	–	–	600	µA	–

Table 17. Fixed SPI AC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID166	F_{SPI}	SPI Operating frequency (Master; 6X oversampling)	–	–	8	MHz	–

Table 18. Fixed SPI Master Mode AC Specifications (Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID167	T_{DMO}	MOSI Valid after SClock driving edge	–	–	15	ns	–
SID168	T_{DSI}	MISO Valid before SClock capturing edge	20	–	–	ns	Full clock, late MISO sampling
SID169	T_{HMO}	Previous MOSI data hold time	0	–	–	ns	Referred to slave capturing edge

Table 19. Fixed SPI Slave Mode AC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID170	T_{DMI}	MOSI Valid before Sclock capturing edge	40	–	–	ns	–
SID171	T_{DSO}	MISO Valid after Sclock driving edge	–	–	$42 + 3 \times T_{CPU}$	ns	$T_{CPU} = 1/F_{CPU}$
SID171A	T_{DSO_EXT}	MISO Valid after Sclock driving edge in Ext Clk mode	–	–	48	ns	–
SID172	T_{HSO}	Previous MISO data hold time	0	–	–	ns	–
SID172A	$T_{SSELSCK}$	SSEL Valid to first SCK Valid edge	100	–	–	ns	–

Internal Low-Speed Oscillator Power Down

Table 25. ILO DC Specifications

(Guaranteed by Design)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID231	I_{ILO1}	I_{LO} operating current	–	0.3	1.05	µA	–
SID233	$I_{ILOLEAK}$	I_{LO} leakage current	–	2	15	nA	–

Table 26. ILO AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID234	$T_{STARTILO1}$	I_{LO} start-up time	–	–	2	ms	Guaranteed by Characterization
SID238	$T_{ILODUTY}$	I_{LO} duty cycle	40	50	60	%	Guaranteed by Characterization
SID.CLK#5	F_{ILO}	I_{LO} frequency	20	40	80	kHz	–

Table 27. PD DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID.PD.1	Rp_std	DFP CC termination for default USB Power	64	80	96	µA	–
SID.PD.2	Rp_1.5A	DFP CC termination for 1.5A power	166	180	194.4	µA	–
SID.PD.3	Rp_3.0A	DFP CC termination for 3.0A power	304	330	356.4	µA	–
SID.PD.4	Rd	UFP CC termination	4.59	5.1	5.61	kΩ	–
SID.PD.5	Rd_DB	UFP (Power Bank) Dead Battery CC Termination on CC1 and CC2	4.08	5.1	6.12	kΩ	All supplies forced to 0V and 1.32 V applied at CC1 or CC2
SID.PD.6	$V_{gndoffset}$	Ground offset tolerated by BMC receiver	–500	–	500	mV	Relative to the remote BMC transmitter.

Table 28. LS-CSA Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID.LSCSA.1	Cin_inp	CSP Input capacitance	7	–	10	pF	Guaranteed by characterization
SID.LSCSA.2	Csa_Acc1	CSA accuracy 5 mV < Vsense < 10 mV	–15	–	15	%	Active Mode
SID.LSCSA.3	Csa_Acc2	CSA accuracy 10 mV < Vsense < 15 mV	–10	–	10	%	
SID.LSCSA.4	Csa_Acc3	CSA accuracy 15 mV < Vsense < 20 mV	–6	–	6	%	
SID.LSCSA.5	Csa_Acc4	CSA accuracy 20 mV < Vsense < 30 mV	–5	–	5	%	
SID.LSCSA.6	Csa_Acc5	CSA accuracy 30 mV < Vsense < 50 mV	–4	–	4	%	
SID.LSCSA.7	Csa_Acc6	CSA accuracy 50 mV < Vsense	–4	–	4	%	
SID.LSCSA.8	Csa_SCP_Acc1	CSA SCP 80 mV	–16.5	–	30	%	
SID.LSCSA.9	Csa_SCP_Acc2	CSA SCP 100 mV	–13.4	–	24	%	
SID.LSCSA.10	Csa_SCP_Acc3	CSA SCP 150 mV	–9.4	–	16	%	
SID.LSCSA.11	Csa_SCP_Acc4	CSA SCP 200 mV	–7.5	–	12	%	
SID.LSCSA.12	Av	Nominal Gain values supported: 5, 10, 20, 35, 50, 75, 125, 150	5	–	150	V/V	
SID.LSCSA.24	Av1_E_Trim	Gain Error	–3	–	3	%	Guaranteed by characterization
SID.LSCSA.31	Av_E_SCP	Gain Error of SCP stage	–3.5	–	3.5	%	Guaranteed by characterization

Table 29. LS-CSA AC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID.LSCSA.AC.1	T_{OCP_GPIO}	Delay from OCP threshold trip to output GPIO toggle	–	–	20	µs	Available on P1.0 or P1.1
SID.LSCSA.AC.2	T_{OCP_Gate}	Delay from OCP threshold trip to external PFET Power Gate Turn off	–	–	50	µs	–
SID.LSCSA.AC.3	T_{SCP_GPIO}	Delay from SCP threshold trip to output GPIO toggle	–	–	15	µs	Available on P1.0 or P1.1
SID.LSCSA.AC.4	T_{SCP_Gate}	Delay from SCP threshold trip to external PFET Power Gate Turn off	–	–	50	µs	–
SID.LSCSA.AC.5	T_{SR_GPIO}	Delay from SR threshold trip to output GPIO toggle	–	–	20	µs	Available on P1.0 or P1.1

Table 30. UV/OV Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID.UVOV.1	V_{THOV1}	Overvoltage Threshold Accuracy, 4.0 V to 11.0 V	–3	–	3	%	Active Mode
SID.UVOV.2	V_{THOV2}	Overvoltage Threshold Accuracy, 11 V to 27.4 V	–3.2	–	3.2	%	
SID.UVOV.3	V_{THUV1}	Undervoltage Threshold Accuracy, 2.7 V to 3.3 V	-4	–	4	%	
SID.UVOV.4	V_{THUV2}	Undervoltage Threshold Accuracy, 3.3 V to 4.0 V	–3.5	–	3.5	%	
SID.UVOV.5	V_{THUV3}	Undervoltage Threshold Accuracy, 4.0 V to 11.0 V	–3	–	3	%	
SID.UVOV.6	V_{THUV4}	Undervoltage Threshold Accuracy, 11.0 V to 22.0 V	–2.9	–	2.9	%	

Table 31. UV/OV AC Specifications

(Guaranteed by Characterization)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID.UVOV.AC.1	T_{OV_GPIO}	Delay from UV threshold trip to output GPIO toggle	–	–	20	µs	Available on P1.0 or P1.1
SID.UVOV.AC.2	T_{OV_GATE}	Delay from UV threshold trip to external PFET power gate turn off	–	–	50	µs	–
SID.UVOV.AC.3	T_{UV_GPIO}	Delay from UV threshold trip to output GPIO toggle	–	–	20	µs	Available on P1.0 or P1.1

Table 34. VBUS Discharge Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details / Conditions
SID.VBUS.DISC.6	I1	20-V NMOS ON current for DS = 1	0.15	–	1	mA	Measured at 0.5 V
SID.VBUS.DISC.7	I2	20-V NMOS ON current for DS = 2	0.4	–	2	mA	
SID.VBUS.DISC.8	I4	20-V NMOS ON current for DS = 4	0.9	–	4	mA	
SID.VBUS.DISC.9	I8	20-V NMOS ON current for DS = 8	2	–	8	mA	
SID.VBUS.DISC.10	I16	20-V NMOS ON current for DS = 16	4	–	10	mA	
SID.VBUS.DISC.11	VBUS_Stop_Error	Error percentage of final V_{BUS} value from setting	–	–	10	%	When V_{BUS} is discharged to 5 V. Guaranteed by Characterization.

Table 35. Voltage (VBUS) Regulation DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details / Conditions
SID.DC.VR.1	$V_{\_IN\_3}$	V(pad_in) at 3-V target	2.85	3	3.15	V	Active mode shunt regulator at 3 V with bandgap
SID.DC.VR.2	$V_{\_IN\_5}$	V(pad_in) at 5-V target	4.75	5	5.25	V	Active mode shunt regulator at 5 V
SID.DC.VR.3	$V_{\_IN\_9}$	V(pad_in) at 9-V target	8.55	9	9.45	V	Active mode shunt regulator at 9 V
SID.DC.VR.4	$V_{\_IN\_15}$	V(pad_in) at 15-V target	14.25	15	15.75	V	Active mode shunt regulator at 15 V
SID.DC.VR.5	$V_{\_IN\_20}$	V(pad_in) at 20-V target	19	20	21	V	Active mode shunt regulator at 20 V
SID.DC.VR.6	$V_{\_IN\_3\_DS}$	V(pad_in) at 3-V target	2.7	3	3.3	V	Deep Sleep mode shunt regulator at 3 V with bandgap
SID.DC.VR.7	$V_{\_IN\_5\_DS}$	V(pad_in) at 5-V target	4.5	5	5.5	V	Deep Sleep mode shunt regulator at 5 V
SID.DC.VR.8	$V_{\_IN\_9\_DS}$	V(pad_in) at 9-V target	8.1	9	9.1	V	Deep Sleep mode shunt regulator at 9 V
SID.DC.VR.9	$V_{\_IN\_15\_DS}$	V(pad_in) at 15-V target	13.5	15	16.5	V	Deep Sleep mode shunt regulator at 15 V
SID.DC.VR.10	$V_{\_IN\_20\_DS}$	V(pad_in) at 20-V target	18	20	22	V	Deep Sleep mode shunt regulator at 20 V
SID.DC.VR.11	I_{KA_OFF}	Off-state cathode current	–	–	10	µA	-
SID.DC.VR.12	I_{KA_ON}	Current through cathode pin	–	–	10	mA	-

Table 36. VBUS Short Protection Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID.VSP.1	V_SHORT_TRIGGER	Short-to-VBUS system-side clamping voltage on the CC/P2.2/P2.3 pins	–	9	–	V	Guaranteed by Characterization.

Table 37. VBUS DC Regulator Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID.VREG.2	VBUS_-DETECT	VBUS detect threshold voltage	1.08	–	2.62	V	–

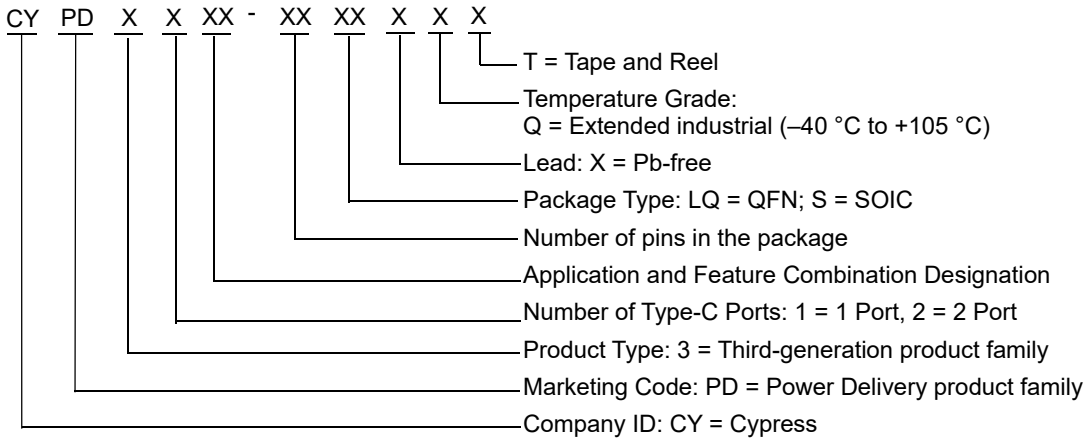
Ordering Information

Table 42 lists the EZ-PD CCG3PA part numbers and features.

Table 42. CCGPA Ordering Information

MPN	Application	Termination Resistor	Role	Bootloader[7]	Package Type	Si ID
CYPD3171-24LQXQ	Power Bank	R_P, R_D, R_{D-DB}	DRP	UFP CC Bootloader	24-Pin QFN	2003
CYPD3174-16SXQ	Power Adapter based on Opto Coupler Feedback	R_P	DFP	DFP CC with Opto Coupler Feedback Bootloader	16-Pin SOIC	2001
CYPD3174-24LQXQ	Power Adapter based on Opto Coupler Feedback	R_P	DFP	DFP CC with Opto Coupler Feedback Bootloader	24-Pin QFN	2000
CYPD3175-24LQXQ	Power Adapter based on Direct Feedback	R_P	DFP	DFP CC with Direct Feedback Bootloader	24-Pin QFN	2002

Ordering Code Definitions



Note
7. It is assumed that VBUS is at 5V by default. Bootloader execution is not responsible for controlling the generation of 5V VBUS.

Packaging

Table 43. Package Characteristics

Parameter	Description	Conditions	Min	Typ	Max	Units
T_A	Operating ambient temperature	Extended Industrial	-40	25	105	°C
T_J	Operating junction temperature	Extended Industrial	-40	25	120	°C
T_{JA}	Package θ_{JA} (24-QFN)	-	-	-	19.98	°C/W
T_{JC}	Package θ_{JC} (24-QFN)	-	-	-	4.78	°C/W
T_{JA}	Package θ_{JA} (16-SOIC)	-	-	-	84	°C/W
T_{JC}	Package θ_{JC} (16-SOIC)	-	-	-	33.9	°C/W

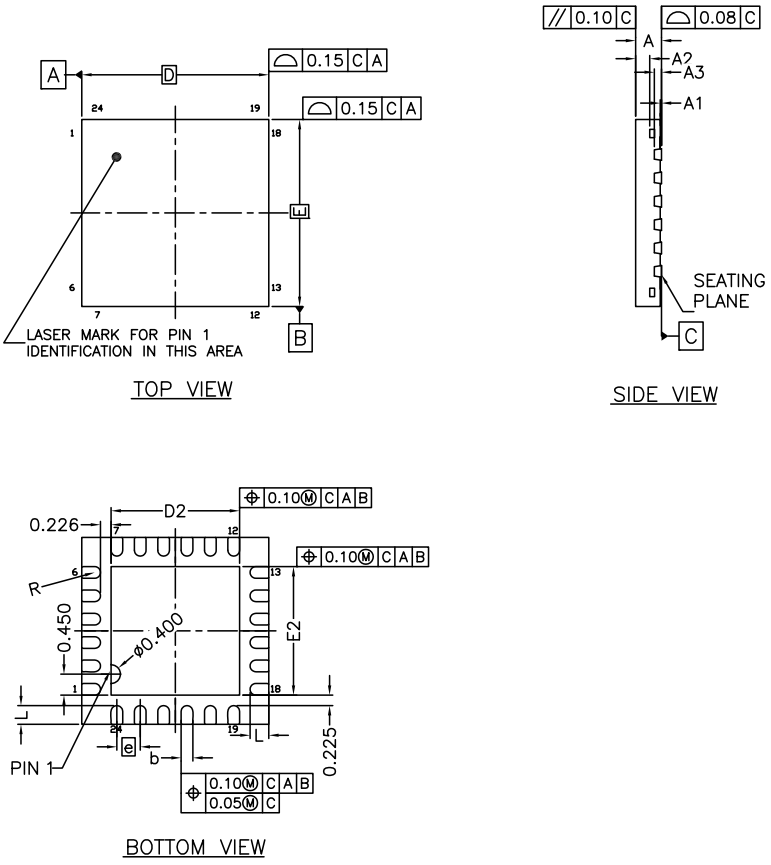
Table 44. Solder Reflow Peak Temperature

Package	Maximum Peak Temperature	Maximum Time within 5° C of Peak Temperature
24-pin QFN	260 ° C	30 seconds
16-pin SOIC	260 ° C	30 seconds

Table 45. Package Moisture Sensitivity Level (MSL), IPC/JEDEC J-STD-2

Package	MSL
24-pin QFN	MSL3
16-pin SOIC	MSL3

Figure 11. 24-pin QFN Package Outline



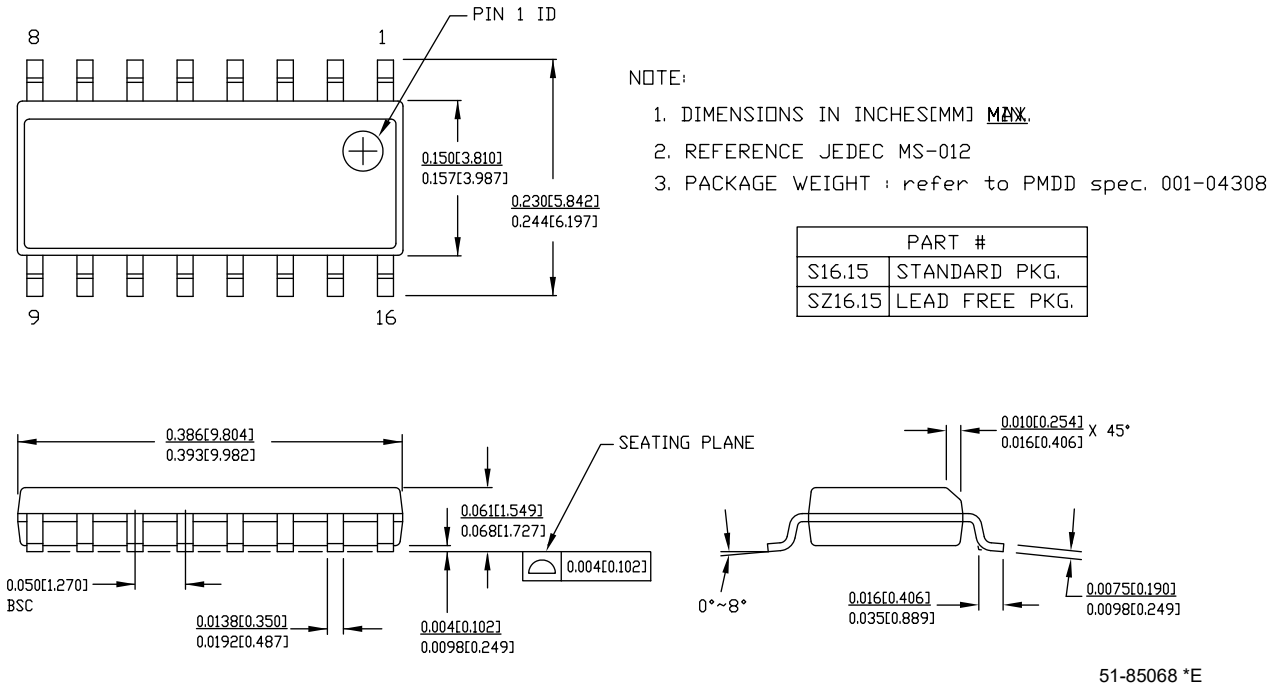
SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	—	—	0.60
A_1	0.00	—	0.05
A_2	—	0.40	0.425
A_3	0.152 REF		
b	0.18	0.25	0.30
D	4.00 BSC		
D_2	2.65	2.75	2.85
E	4.00 BSC		
E_2	2.65	2.75	2.85
L	0.30	0.40	0.50
e	0.50 BSC		
R	0.09	—	—

NOTES

1. ALL DIMENSIONS ARE IN MILLIMETERS.
2. DIE THICKNESS ALLOWABLE IS 0.305 mm MAXIMUM(.012 INCHES MAXIMUM)
3. DIMENSIONING & TOLERANCES CONFORM TO ASME Y14.5M. -1994.
4. THE PIN #1 IDENTIFIER MUST BE PLACED ON THE TOP SURFACE OF THE PACKAGE BY USING INDENTATION MARK OR OTHER FEATURE OF PACKAGE BODY.
5. EXACT SHAPE AND SIZE OF THIS FEATURE IS OPTIONAL.
6. PACKAGE WARPAGE MAX 0.08 mm.
7. APPLIED FOR EXPOSED PAD AND TERMINALS. EXCLUDE EMBEDDING PART OF EXPOSED PAD FROM MEASURING.
8. APPLIED ONLY TO TERMINALS.
9. JEDEC SPECIFICATION NO. REF: N.A.

002-16934 *A

Figure 12. 16-pin SOIC Package Outline



Document History Page

Document Title: EZ-PD™ CCG3PA Datasheet, USB Type-C Port Controller Document Number: 002-16951				
Revision	**ECN**	**Orig. of Change**	**Submission Date**	**Description of Change**
**	5473667	VGT	10/13/2016	New datasheet
*A	5544333	VGT	12/13/2016	Changed datasheet status to Preliminary. Updated Features. Updated Logic Block Diagram. Updated Functional Overview Updated Figure 2, Figure 3, Figure 6, Figure 8, Figure 9, and Figure 10. Updated Pinouts. Updated Table 4 with VCC_PIN_ABS and VSBU_PIN_ABS parameters. Added Q-temp parts in Table 42.
*B	5583660	VGT	01/18/2017	Updated General Description, Features, I/O Subsystem, CPU, Charger Detection, and Ordering Information. Updated Table 2 and Table 4. Updated Figure 6 through Figure 10. Updated Sales page.
*C	5665676	VGT	03/22/2017	Updated Figure 2, Figure 6, Figure 8, Figure 10, Table 1,Table 2, Table 4, Table 42, Features, Logic Block Diagram, Functional Overview, Power Systems Overview, Ordering Code Definitions, Acronyms. Added Internal Block Diagram. Added Table 5 through Table 41 in Device-Level Specifications. Updated compliance with USB spec in Sales, Solutions, and Legal Information. Updated Cypress logo.
*D	5738854	VGT	05/19/2017	Added Application Diagram description before Figure 6, Figure 8, Figure 9, and Figure 10. Added Figure 1. Added CCG3PA Programming and Bootloading section. Added Document History Page section. Added Table 3. Updated Figure 3, Figure 4, Figure 6, Figure 8, Figure 9, and Figure 10. Updated Table 2, Table 4, Table 5, and Table 42. Updated Figure 11 (spec 002-16934 Rev. ** to *A) in Packaging. Updated Cypress logo, Sales page, and Copyright information.
*E	5984670	VGT	12/06/2017	Removed Preliminary document status. Updated System-Level Fault Protection, Power, and System-Level ESD Protection. Updated Internal Block Diagram Updated Figure 2. Table 2: Updated Pins 12 and 13. Added Note 5. Updated Figure 6. Added Figure 7. Table 4: Updated max value for $V_{CC\_PIN\_ABS}$ Table 5: Removed SID_DS and updated typ value for SID_PB_DS_UA. Table 7: Added new SID.GIO#17 spec and changed SID.GIO#17 to SID.GIO#17A. Added Table 9 and Table 10. Table 12: Updated max value for SID149. Table 22; Added “Guaranteed by Characterization” Table 24: Updated Conditions for SID226 and SID228. Updated typ value and conditions for SID.CLK#1. Table 26: Updated Conditions for SID234 and SID238. Table 28: Updated min, typ, and max values for SID.LSCSA.1,SID.LSCSA.7, and SID.LSCSA.24 Updated Conditions for SID.GIO#17A, SID.GIO#43, SID.GIO#44, SID.GIO#45, and SID69. Table 31: Added “Guaranteed by Characterization” Table 32: Added SID.GD.9, SID.GD.10, SID.GD.11, SID.GD.12, SID.GD.13, SID.GD.14. Changed description of spec IDs SID.GD.1 to SID.GD.8. Table 33: Renumbered all spec IDs starting from SID.GD.15 to SID.GD.20. Modified max values of SID.GD.15, SID.GD.17 and SID.GD.18. Modified Details/Conditions of all parameters. Table 34: Removed spec IDs SID.VBUS.DISC.1 to SID.VBUS.DISC5. Renumbered SID.VBUS.DISC6 to SID.VBUS.DISC11. Added new spec IDs SID.VBUS.DISC6 to SID.VBUS.DISC10.

Document Title: EZ-PD™ CCG3PA Datasheet, USB Type-C Port Controller Document Number: 002-16951				
*E (contd)	5984670	VGT	12/06/2017	Table 35: Added V_IN_3 and V_IN3_DS parameters and renumbered spec IDs from SID.DC.VR.1 to SID.DC.VR.12. Added Table 36. Table 39: Updated min and max values for SID.ADC.4. Table 42: Added new MPN CYPD3174-24LQXQ. Modified "Application" column of CYPD3174-16SXQ and CYPD3175-24LQXQ MPNs. Removed Errata. Added Table 43, Table 44 and Table 45 to Packaging section.
*F	6079226	VGT	03/02/2018	Added “The voltage reference for the ADCs is generated either from the VDDD supply or from internal bandgap. When sensing the GPIO pin voltage with an ADC, the pin voltage cannot exceed the VDDIO supply value” to ADC section. Table 2: Updated the Descripion “GPIO with Open drain with pull-up assist. Configurable as GPIO_20VT/I2C_SDA_1/IEC. Tolerant to temporary short to VBUS pin” for Pins P2.2 and P2.3. Table 7: Removed SBU1, SBU2 reference in Details/Conditions for Spec ID SID.GIO#17. Table 32: Moved “0.003” to Typ column for the Spec ID SID.GD.9 and SID.GD.10. Table 12: Updated typical and max values for II2C4 parameter. Table 9: Removed GPIO_20VT_Voh parameter. Table 28: Updated max values of Csa_SCP_Acc parameters. Table 39: Updated the Description of Spec ID SID.ADC.6 as “ADC reference voltage when generated from band gap.”. Removed SID.ADC.5 parameter and added SID.ADC.2A and SID.ADC.3A parameters. Updated Details/Conditions of SID.ADC.2 and SID.ADC3 parameters. Table 35: Added units (V) to SID.DC.VR.3, SID.DC.VR.4 and SID.DC.VR.5 parameters. Updated VBUS Short Protection and I/O Subsystem sections. Updated Table 3 with information on Fault Indicator and VBUS Short Protection Capability. Updated Application Diagrams section.